

# μPA2815T1S

P-channel MOSFET

-30 V, -21 A, 11 mΩ

R07DS0777EJ0101

Rev.1.01

May 28, 2013

## Description

The μPA2815T1S is P-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipment.

## Features

- $V_{DSS} = -30\text{ V}$  ( $T_A = 25^\circ\text{C}$ )
- Low on-state resistance  
—  $R_{DS(on)} = 11\text{ m}\Omega\text{ MAX.}$  ( $V_{GS} = -10\text{ V}$ ,  $I_D = -21\text{ A}$ )
- 4.5 V Gate-drive available
- Small & thin type surface mount package with heat spreader
- Pb-free and Halogen free



HWSO8

## Ordering Information

Part No.	Lead Plating	Packing	Package
μPA2815T1S-E2-AT *1	Pure Sn	Tape 5000 p/reel	HWSO8 typ. 0.022 g

Note: \*1. Pb-free (This product does not contain Pb in external electrode and other parts.)

## Absolute Maximum Ratings ( $T_A = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS} = 0\text{ V}$ )	$V_{DSS}$	-30	V
Gate to Source Voltage ( $V_{DS} = 0\text{ V}$ )	$V_{GSS}$	±20	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	±21	A
Drain Current (pulse) *1	$I_{D(pulse)}$	±84	A
Total Power Dissipation *2	$P_{T1}$	1.5	W
Total Power Dissipation (PW = 10 sec) *2	$P_{T2}$	3.8	W
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T3}$	14.5	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C
Single Avalanche Current *3	$I_{AS}$	19	A
Single Avalanche Energy *3	$E_{AS}$	36.1	mJ

## Thermal Resistance

Channel to Ambient Thermal Resistance *2	$R_{th(ch-A)}$	83.3	°C/W
Channel to Case (Drain) Thermal Resistance	$R_{th(ch-C)}$	8.6	°C/W

Notes: \*1.  $PW \leq 10\ \mu\text{s}$ , Duty Cycle  $\leq 1\%$

\*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mm

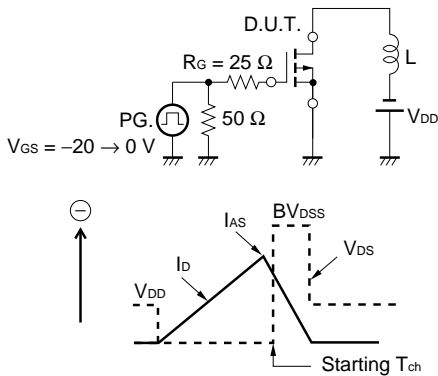
\*3. Starting  $T_{ch} = 25^\circ\text{C}$ ,  $V_{DD} = -15\text{ V}$ ,  $R_G = 25\ \Omega$ ,  $V_{GS} = -20 \rightarrow 0\text{ V}$ ,  $L = 100\ \mu\text{H}$

**Electrical Characteristics (T<sub>A</sub> = 25°C)**

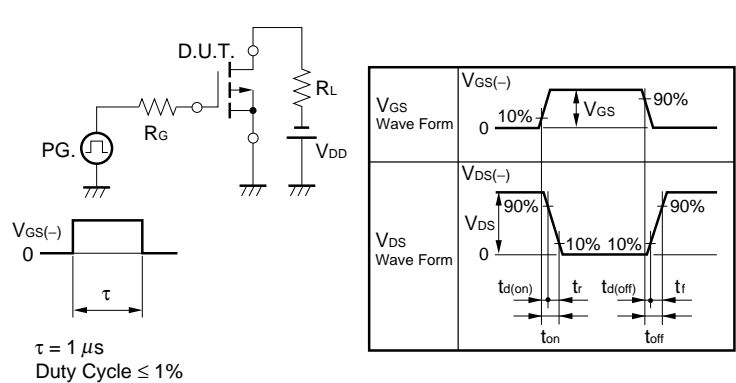
Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I <sub>DS</sub>			-1	μA	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V
Gate Leakage Current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Gate Cut-off Voltage	V <sub>GS(off)</sub>	-1.0		-2.5	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance *1	y <sub>fs</sub>	15			S	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -10.5 A
Drain to Source On-state Resistance *1	R <sub>DS(on)1</sub>		9	11	mΩ	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -21 A
	R <sub>DS(on)2</sub>		16	23	mΩ	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -10.5 A
Input Capacitance	C <sub>iSS</sub>		1760		pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz
Output Capacitance	C <sub>oSS</sub>		850		pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>		750		pF	
Turn-on Delay Time	t <sub>d(on)</sub>		13		ns	V <sub>DD</sub> = -15 V, I <sub>D</sub> = -10.5 A, V <sub>GS</sub> = -10 V, R <sub>G</sub> = 10 Ω
Rise Time	t <sub>r</sub>		40		ns	
Turn-off Delay Time	t <sub>d(off)</sub>		88		ns	
Fall Time	t <sub>f</sub>		171		ns	
Total Gate Charge	Q <sub>G</sub>		47		nC	V <sub>DD</sub> = -24 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -21 A
Gate to Source Charge	Q <sub>GS</sub>		4.2		nC	
Gate to Drain Charge	Q <sub>GD</sub>		24		nC	
Body Diode Forward Voltage *1	V <sub>F(S-D)</sub>		0.9		V	I <sub>F</sub> = 21 A, V <sub>GS</sub> = 0 V
Reverse Recovery Time	t <sub>rr</sub>		166		ns	I <sub>F</sub> = 21 A, V <sub>GS</sub> = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q <sub>rr</sub>		222		nC	

Note: \*1. Pulsed

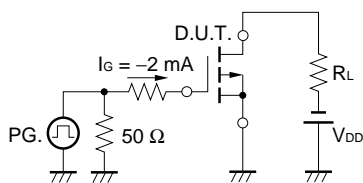
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**

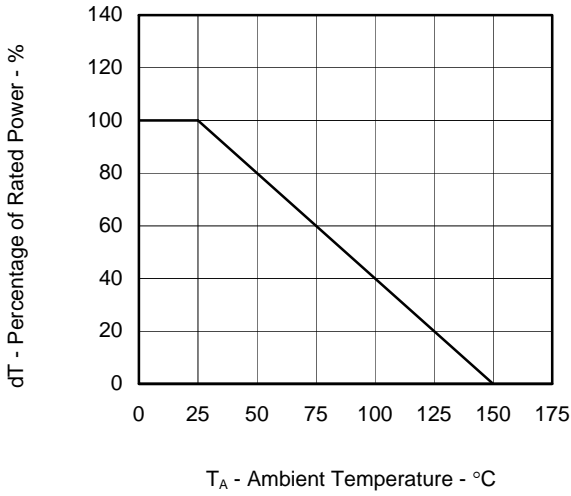


**TEST CIRCUIT 3 GATE CHARGE**

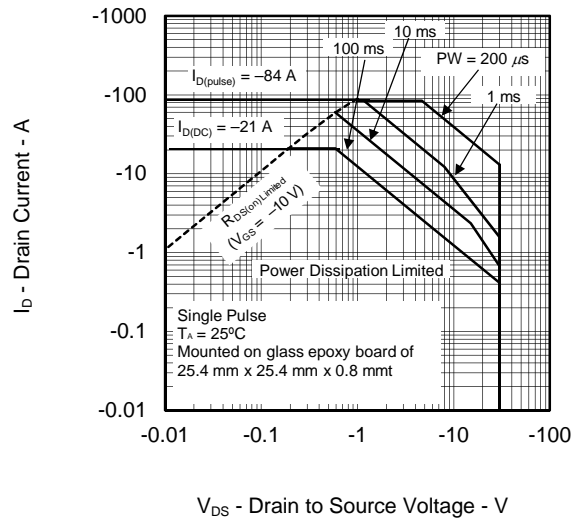


Typical Characteristics (T<sub>A</sub> = 25°C)

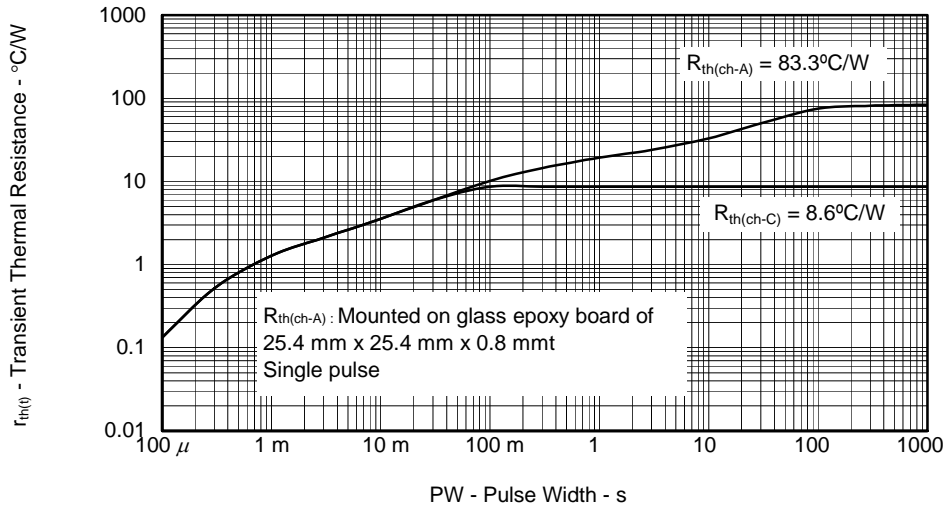
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



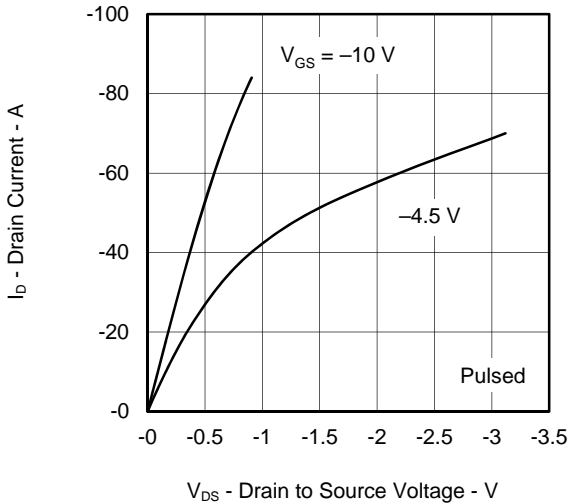
FORWARD BIAS SAFE OPERATING AREA



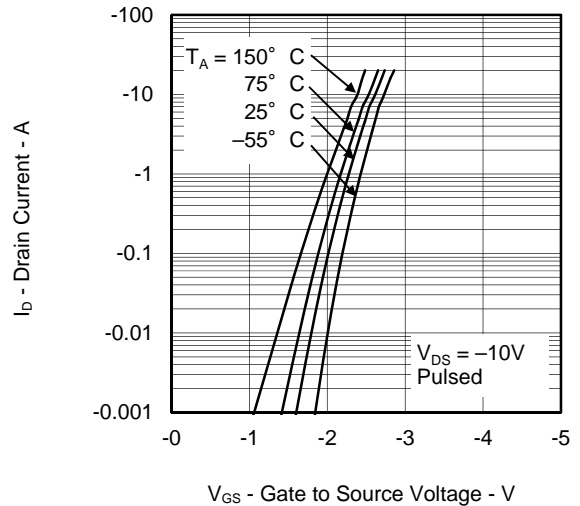
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



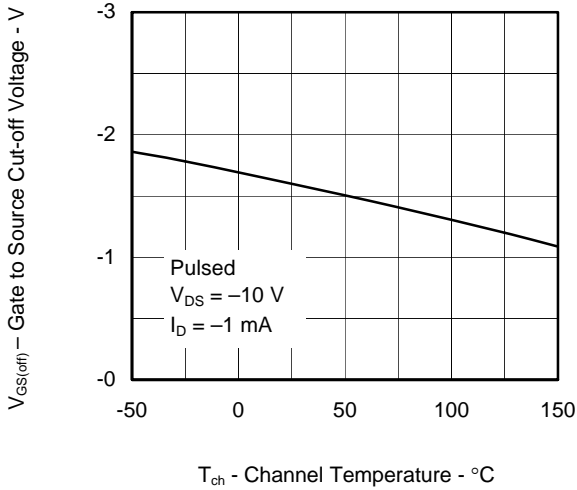
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



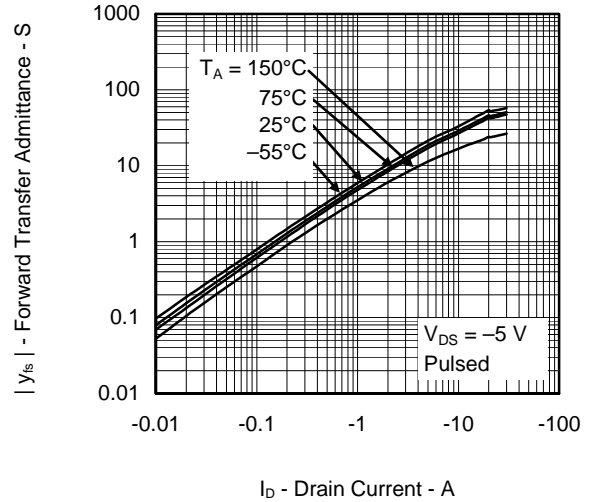
FORWARD TRANSFER CHARACTERISTICS



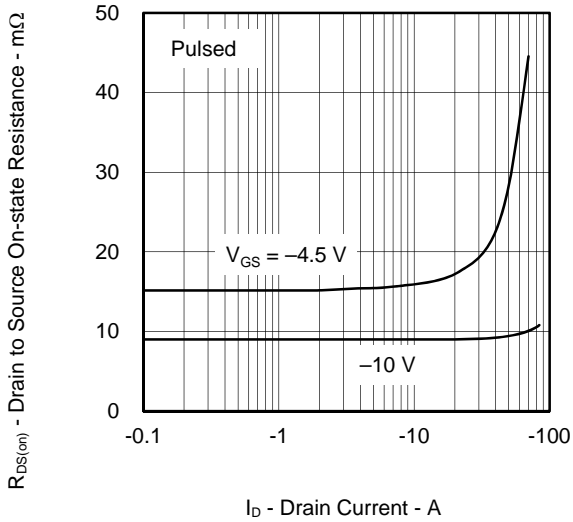
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



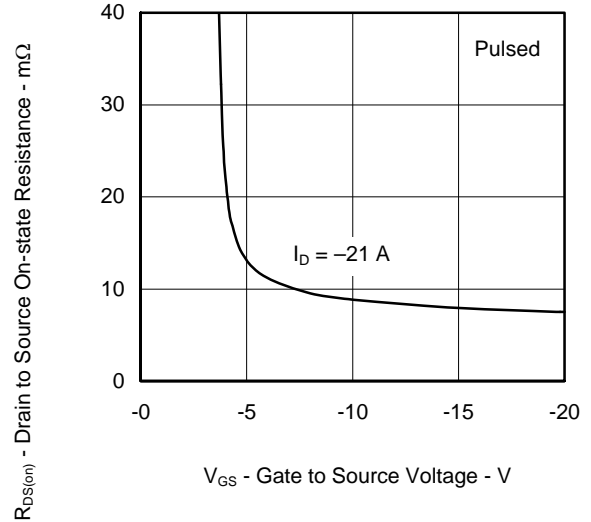
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



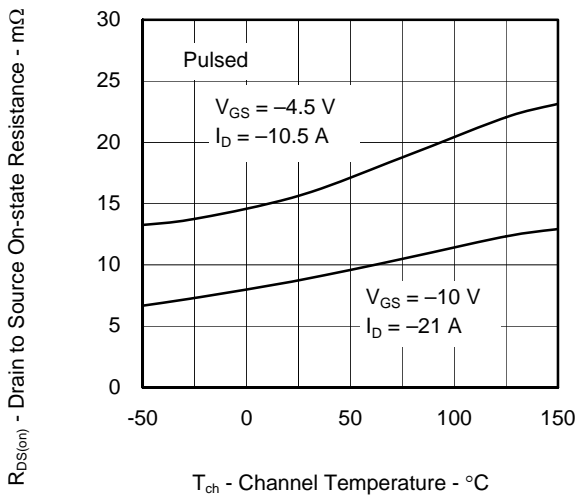
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



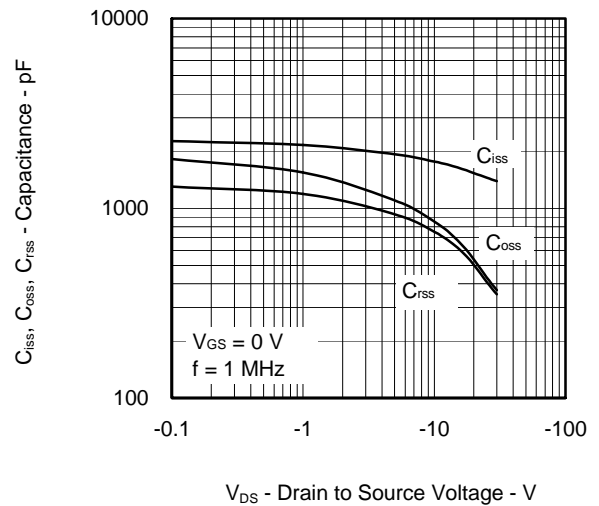
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



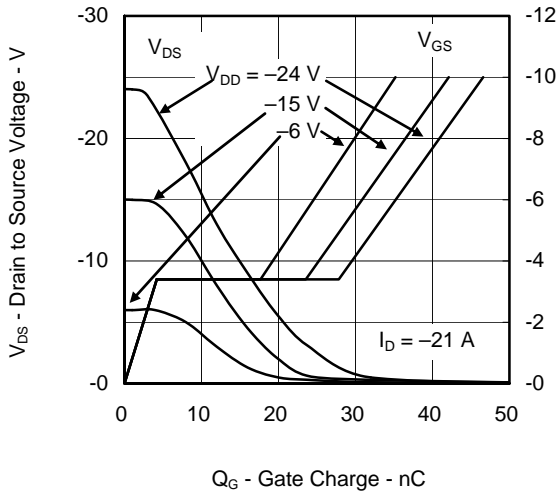
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



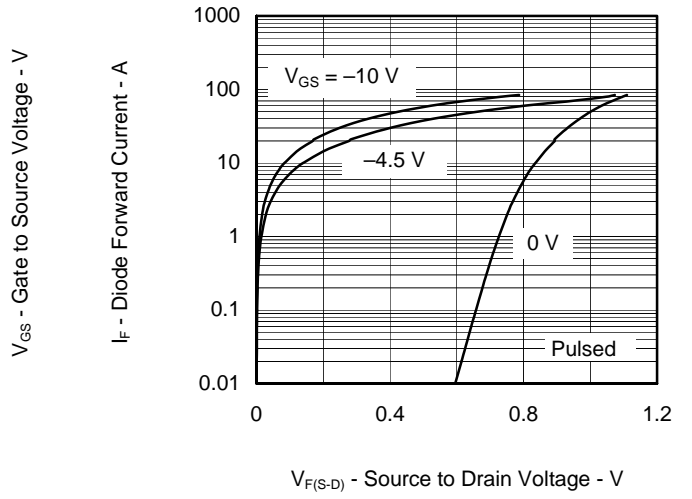
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



**DYNAMIC INPUT/OUTPUT CHARACTERISTICS**

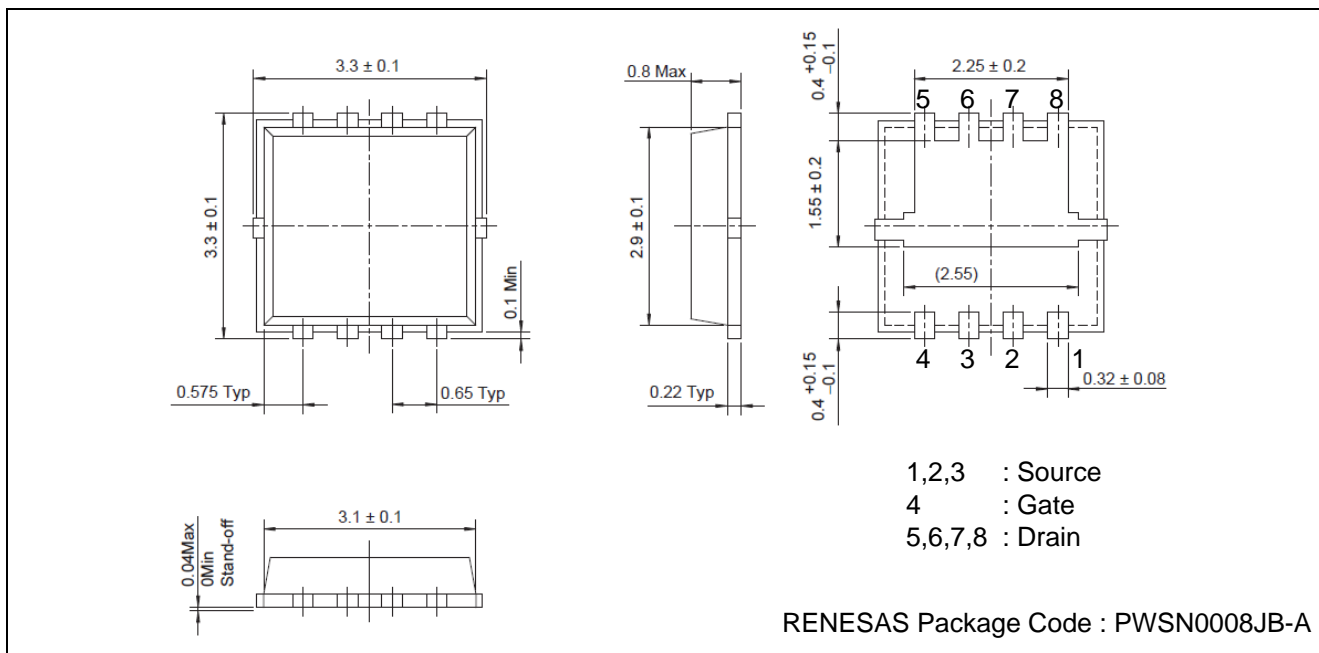


**SOURCE TO DRAIN DIODE FORWARD VOLTAGE**

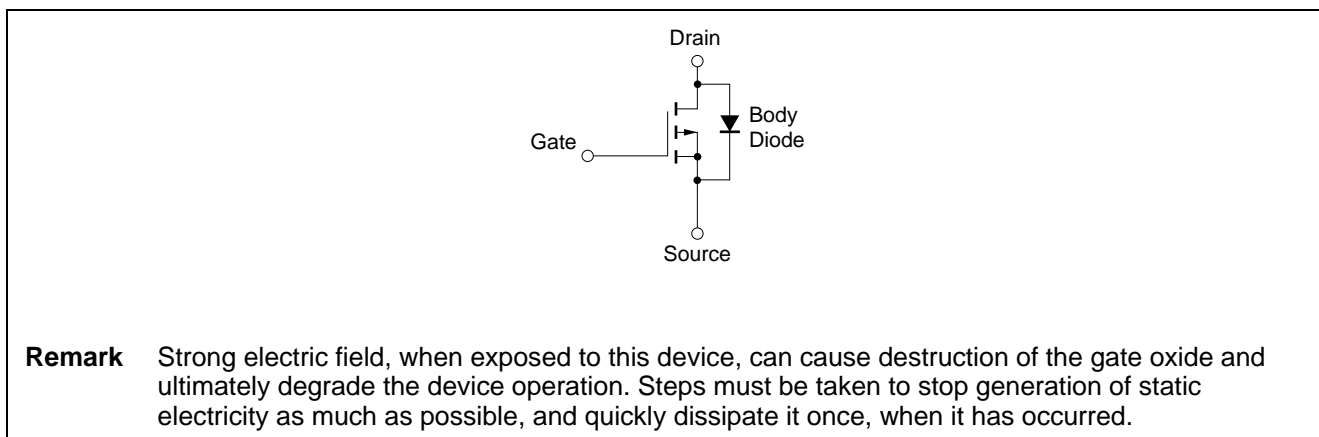


### Package Drawings (Unit: mm)

#### HWSO-8



### Equivalent Circuit



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2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.  
Tel: +1-408-588-6000, Fax: +1-408-588-6130

**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
Tel: +1-905-898-5441, Fax: +1-905-898-3220

**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-651-700, Fax: +44-1628-651-804

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

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Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
13F, No. 363, Fu Shing North Road, Taipei, Taiwan  
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

**Renesas Electronics Singapore Pte. Ltd.**  
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949  
Tel: +65-6213-0200, Fax: +65-6213-0300

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**Renesas Electronics Korea Co., Ltd.**  
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